



PATENT APPLICATION

**FILING UNDER 37 CFR §1.312
EXPEDITED PROCEDURE
TECHNOLOGY CENTER ART UNIT 1722**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

ATTN: OFFICE OF PUBLICATIONS

Izumi FUSEGAWA et al.

Notice of Allowance Mailed 09/25/07 -
Batch/Confirmation No. 5592

Application No.: 10/568,186

Group Art Unit: 1722

Filed: February 13, 2006

Examiner: F. HITESHEW

Docket No.: 126961

For: METHOD FOR PRODUCING A SINGLE CRYSTAL AND SILICON SINGLE
CRYSTAL WAFER

COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

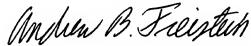
Sir:

In reply to the Examiner's Statement of Reasons for Allowance in the Notice of
Allowance mailed September 25, 2007, please consider the following remarks.

The Examiner's Statement for Reasons for Allowance states: "the most relevant prior
art or reference cited was that of Mitamura et al. in view of W0 01/81661 A1." However,
Applicants argued that Mitamura et al. cannot be used as a prior art reference. Secondly, in
the Reasons for Allowance at page 2, paragraph 2, line 5, the term "downward" is included as
a feature of the claimed invention. However, claim 7, nor any other allowed claim, includes
the feature "downward." Applicants respectfully request a corrected or supplemental Notice
of Allowance with the indicated corrections.

The Examiner is invited to contact the undersigned at the telephone number set forth below regarding any matter concerning this application.

Respectfully submitted,



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JAO:ABF/hms

Date: November 5, 2007

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